



| INTERNAL NTC - THERMISTOR SPECIFICATIONS | | | | |
|--|--------------------|--|------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUE | UNITS |
| Resistance | R ₂₅ | T _C = 25 °C | 5000 | Ω |
| | R ₁₀₀ | T _C = 100 °C | 493 ± 5 % | |
| B-value | B _{25/50} | R ₂ = R ₂₅ exp. [B _{25/50} (1/T ₂ - 1/(298.15 K))] | 3375 ± 5 % | K |
| Maximum operating temperature | | | 220 | °C |
| Dissipation constant | | | 2 | mW/°C |
| Thermal time constant | | | 8 | s |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | |
|--|-------------------|------|-------|------|-------|
| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNITS |
| IGBT - junction-to-case (per switch) | R _{thJC} | - | - | 0.14 | °C/W |
| DIODE - junction-to-case (per diode) | R _{thJC} | - | - | 0.3 | |
| Case to sink, flat, greased surface (per module) | R _{thJS} | - | 0.015 | - | |
| Mounting torque (M5) | | 3.0 | - | 6.0 | Nm |
| Weight | | - | 290 | - | g |

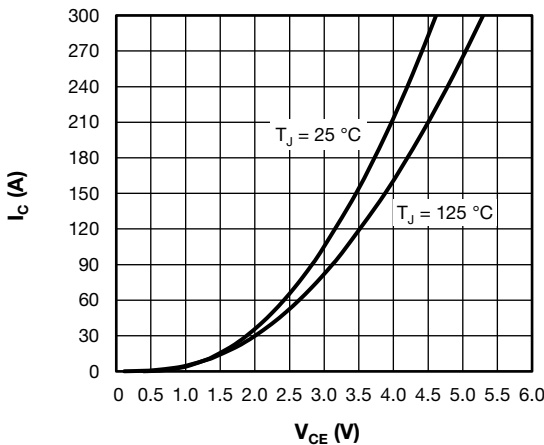


Fig. 1 - Typical IGBT Output Characteristics, V_{GE} = 15 V

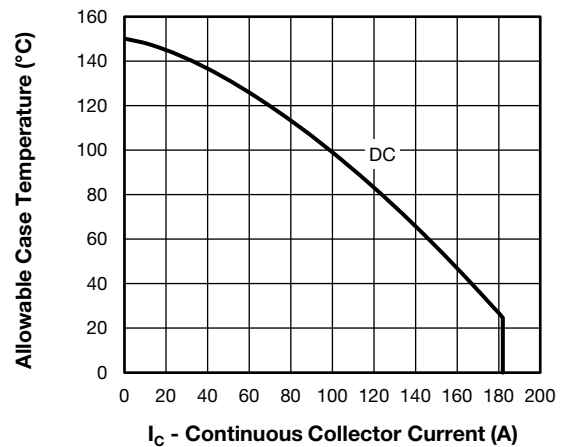


Fig. 3 - Maximum IGBT Continuous Collector Current vs. Case Temperature

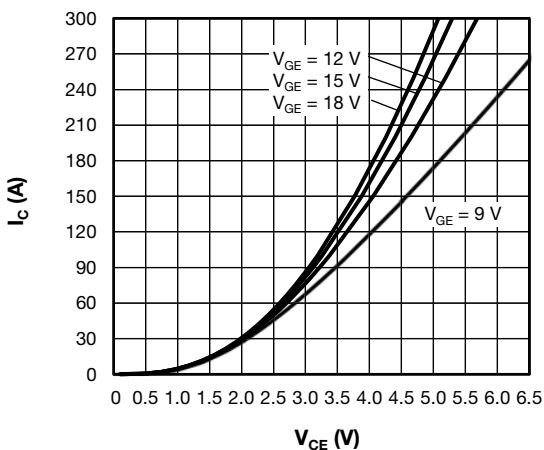


Fig. 2 - Typical IGBT Output Characteristics, T_J = 125 °C

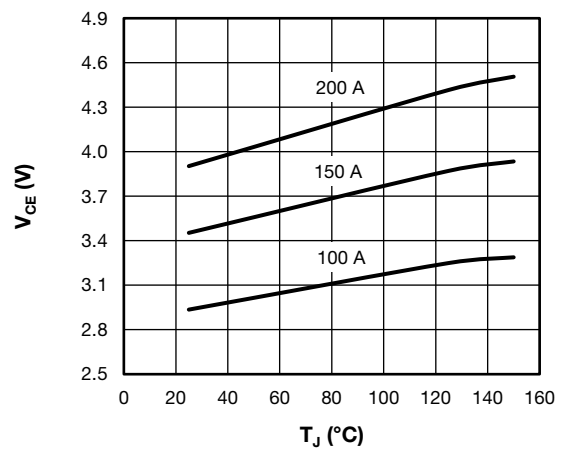


Fig. 4 - Collector to Emitter Voltage vs. Junction Temperature

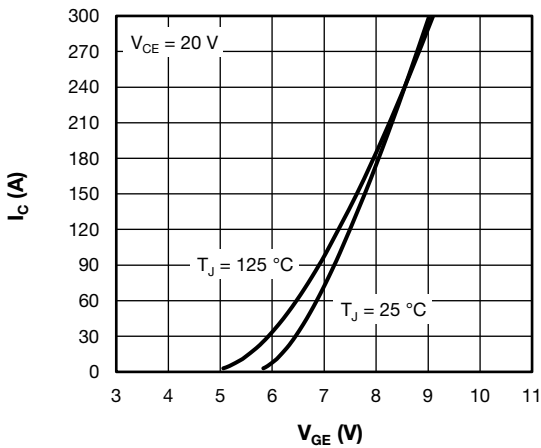


Fig. 5 - Typical IGBT Transfer Characteristics

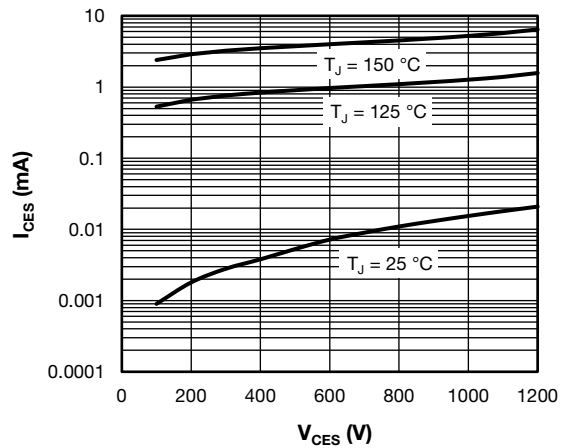


Fig. 8 - Typical IGBT Zero Gate Voltage Collector Current

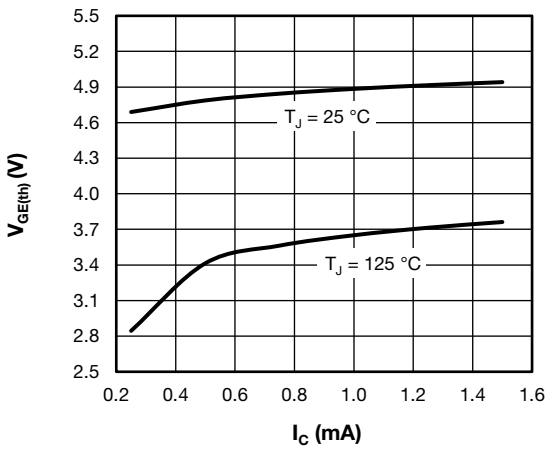


Fig. 6 - Typical IGBT Gate Threshold Voltage

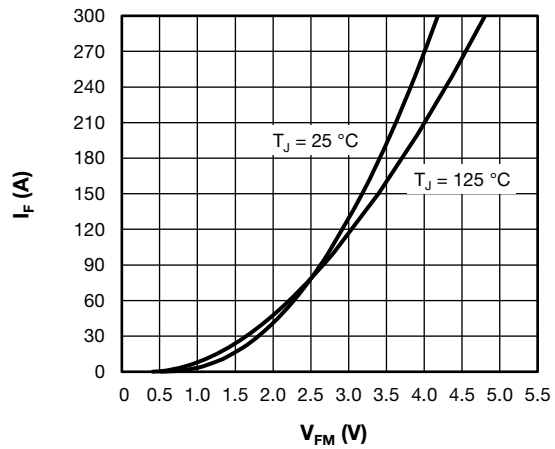


Fig. 9 - Typical Diode Forward Characteristics

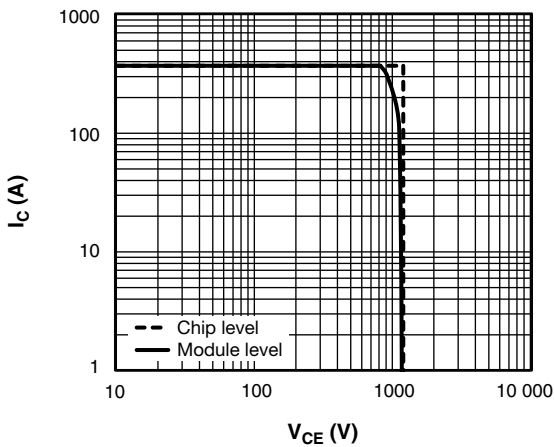


Fig. 7 - IGBT Reverse BIAS SOA $T_J = 150\text{ }^\circ\text{C}$, $V_{GE} = 15\text{ V}$

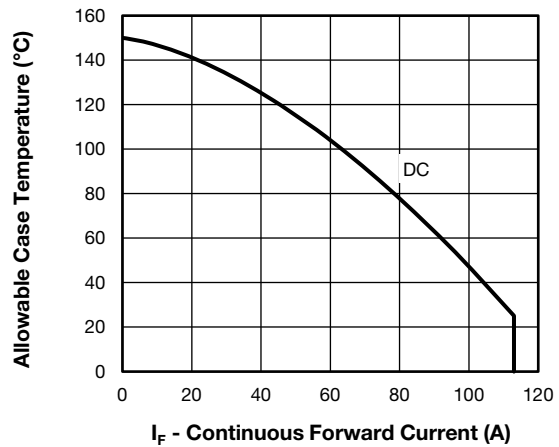


Fig. 10 - Maximum Diode Continuous Forward Current vs. Case Temperature